Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Low threshold voltage
- Trench MOSFET technology
- Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 500 V HBM (class H1B)
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V	
V_{GS}	gate-source voltage			-8	-	8	V	
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	5	Α	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	28	33	mΩ	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	15776	D
2	D	drain		
3	G	gate	2 5	G ✓ ↓ ★ \
4	S	source	3 8 4	· · · · · · · · · · · · · · · · · · ·
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6	s
7	D	drain	(SOT1220)	017aaa255
8	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package	^P ackage							
	Name	Description	Version						
PMPB29XNEA		DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220						

7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB29XNEA	4H

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	5	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	3.2	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	12	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.7	W
		T _{sp} = 25 °C		-	12.5	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode		'			
I _S	source current	T _{amb} = 25 °C	[1]	-	1.9	Α
ESD maxim	um rating		'	'	'	
V _{ESD}	electrostatic discharge voltage	НВМ	[2]	-	500	V
Avalanche r	uggedness	-	'	'	'	
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 0.75 A; DUT in avalanche (unclamped)		-	11.8	mJ

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Measured between all pins.

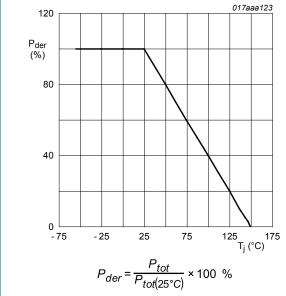
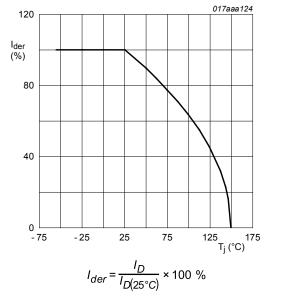


Fig. 1. Normalized total power dissipation as a function of junction temperature



ig. 2. Normalized continuous drain current as a function of junction temperature

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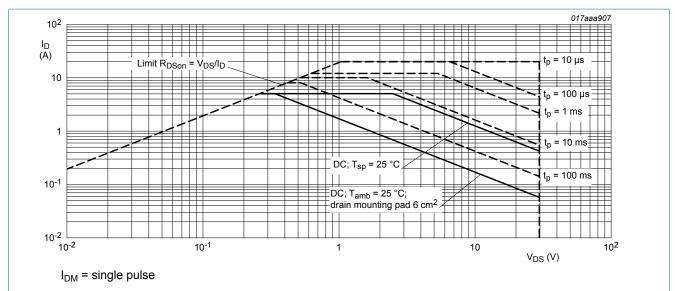


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

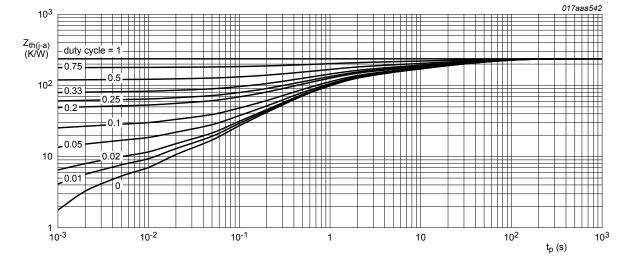
30 V, N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

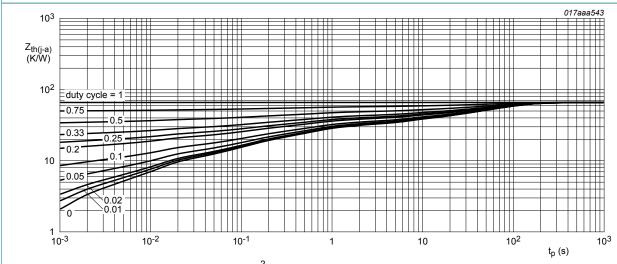
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient	in free air	[1]	-	235	270	K/W	
	junction to ambient		[2]	-	67	74	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30 V, N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 μ A; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.4	0.65	0.9	V
I _{DSS}	drain leakage current	V _{DS} = 20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
R _{DSon} c	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}$	-	28	33	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 5 A; T _j = 150 °C	-	46	54	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 3 \text{ A}; T_j = 25 \text{ °C}$	-	32	40	mΩ
		V _{GS} = 1.8 V; I _D = 1.9 A; T _j = 25 °C	-	37	50	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}$	-	30	-	S
R_{G}	gate resistance	f = 1 MHz; T _j = 25 °C	-	1.8	-	Ω
Dynamic ch	aracteristics		,			
Q _{G(tot)}	total gate charge	$V_{DS} = 15 \text{ V}; I_D = 5 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	12.4	18.6	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	1.2	-	nC
Q_{GD}	gate-drain charge		-	2.1	-	nC
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	1150	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	110	-	pF
C _{rss}	reverse transfer capacitance		-	85	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 5 A; V _{GS} = 4.5 V;	-	8	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	17	-	ns
t _{d(off)}	turn-off delay time		-	33	-	ns
t _f	fall time]	-	32	-	ns
Source-drai	in diode		1			
V_{SD}	source-drain voltage	$I_S = 1.9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.6	1.2	V
t _{rr}	reverse recovery time	$I_S = 1.9 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	9	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; T_j = 25 \text{ °C}$	-	2	-	nC

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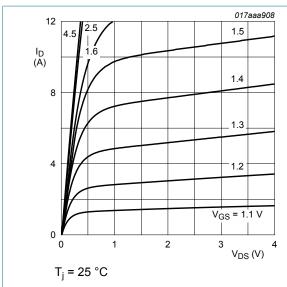


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

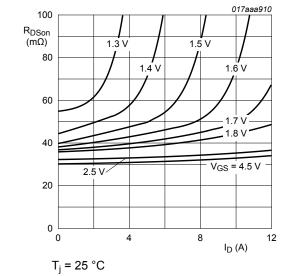


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

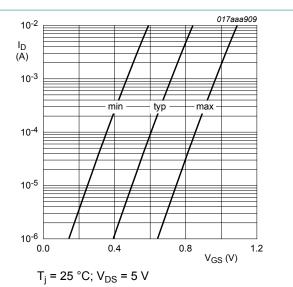


Fig. 7. Subthreshold drain current as a function of gate-source voltage

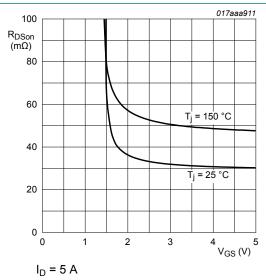


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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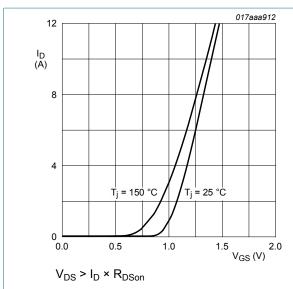


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

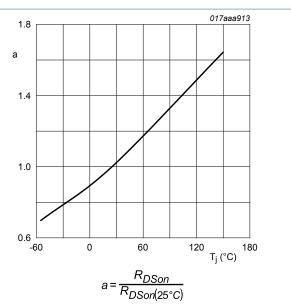


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

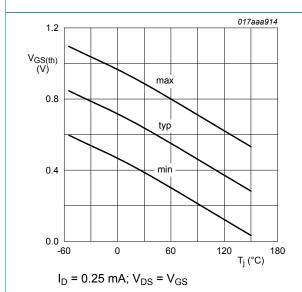


Fig. 12. Gate-source threshold voltage as a function of junction temperature

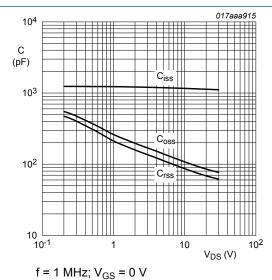


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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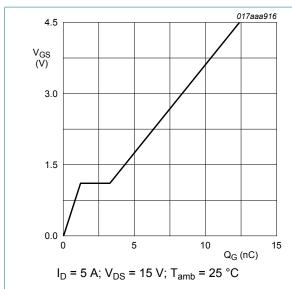


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

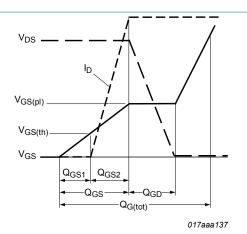


Fig. 15. MOSFET transistor: Gate charge waveform definitions

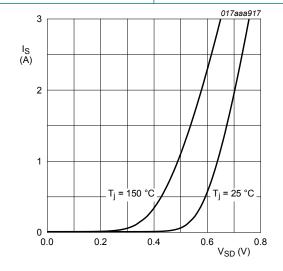
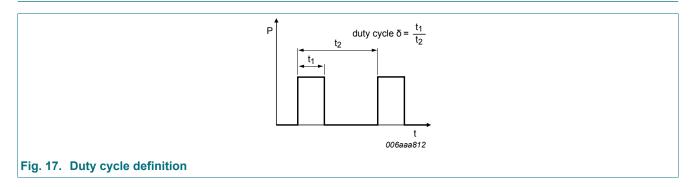


Fig. 16. Source current as a function of source-drain voltage; typical values

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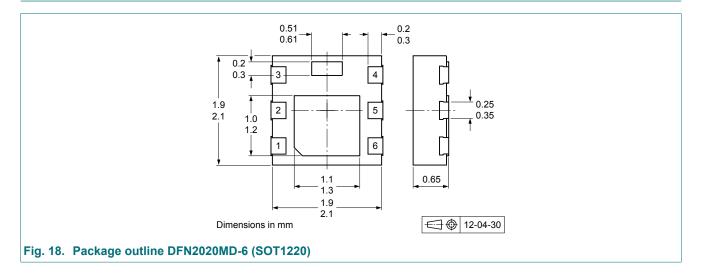
11. Test information



Quality information

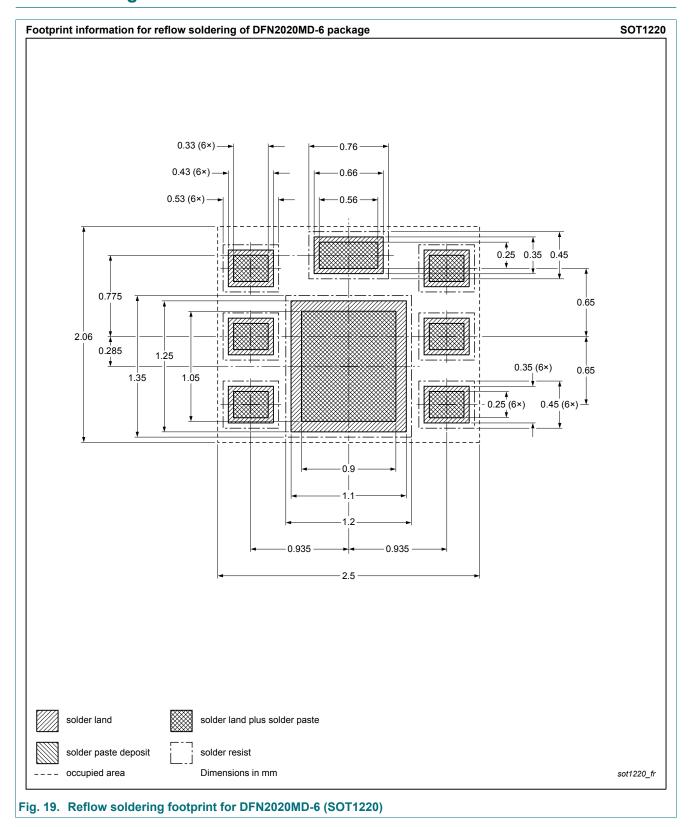
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



30 V, N-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB29XNEA v.1	20180910	Product data sheet	-	-

30 V, N-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PMPB29XNEA

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